

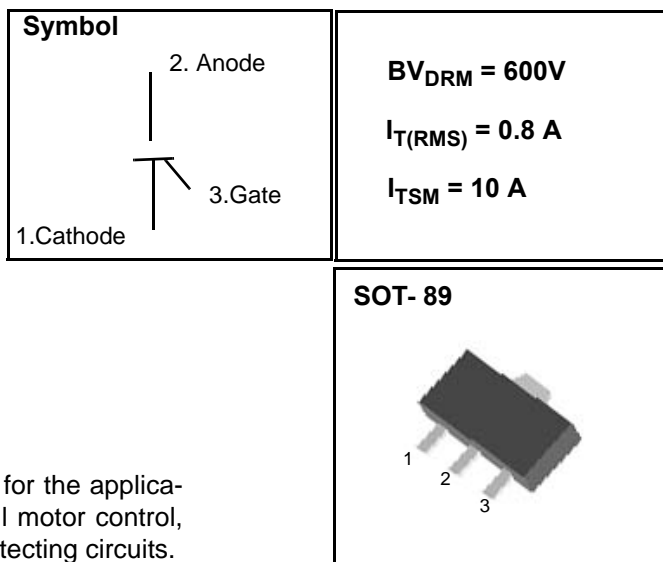
Sensitive Gate Silicon Controlled - Rectifiers

Features

Repetitive Peak Off-State Voltage : 400V
R.M.S On-State Current ($I_{T(RMS)} = 0.8 \text{ A}$)
Low On-State Voltage (1.2V(Typ.)@ I_{TM})
Available with tape & reel

General Description

Sensitive-gate triggering thyristor is suitable for the application where gate current limited such as small motor control, gate driver for large thyristor, sensing and detecting circuits.



Absolute Maximum Ratings ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Condition	Ratings	Units
V_{DRM}	Repetitive Peak Off-State Voltage	sine wave, 50 to 60Hz, gate open	400	V
$I_{T(AV)}$	Average On-State Current	half sine wave : $T_C = 112^\circ\text{C}$	0.5	A
$I_{T(RMS)}$	R.M.S On-State Current	180° Conduction Angle	0.8	A
I_{TSM}	Surge On-State Current	1/2 Cycle, 60Hz, sine wave non-repetitive , $t = 8.3\text{ms}$	10	A
I^2t	I^2t for Fusing	$t = 8.3\text{ms}$	0.415	A^2s
P_{GM}	Forward Peak Gate Power Dissipation	$T_A = 25^\circ\text{C}$, pulse width $1.0\mu\text{s}$	2	W
$P_{G(AV)}$	Forward Average Gate Power Dissipation	$T_A = 25^\circ\text{C}$, $t = 8.3\text{ms}$	0.1	W
I_{FGM}	Forward Peak Gate Current	$T_A = 25^\circ\text{C}$, pulse width $1.0\mu\text{s}$	1	A
V_{RGM}	Reverse Peak Gate Voltage	$T_A = 25^\circ\text{C}$, pulse width $1.0\mu\text{s}$	5.0	V
T_J	Operating Junction Temperature		- 40 ~ 125	$^\circ\text{C}$
T_{STG}	Storage Temperature		- 40 ~ 150	$^\circ\text{C}$

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Electrical Characteristics ($T_C = 25\text{ }^\circ\text{C}$ unless otherwise noted)

Symbol	Items	Conditions	Ratings			Unit
			Min.	Typ.	Max.	
I_{DRM}	Repetitive Peak Off-State Current	$V_{\text{AK}} = V_{\text{DRM}}$ or V_{RRM} ; $R_{\text{GK}} = 1000$ $T_C = 25\text{ }^\circ\text{C}$ $T_C = 125\text{ }^\circ\text{C}$			10 200	μA
V_{TM}	Peak On-State Voltage (1)	($I_{\text{TM}} = 1\text{ A}$, Peak)		1.2	1.7	V
I_{GT}	Gate Trigger Current (2)	$V_{\text{AK}} = 6\text{ V}$, $R_L = 100$ $T_C = 25\text{ }^\circ\text{C}$ $T_C = -40\text{ }^\circ\text{C}$			200 500	μA
V_{GT}	Gate Trigger Voltage (2)	$V_D = 7\text{ V}$, $R_L = 100$ $T_C = 25\text{ }^\circ\text{C}$ $T_C = -40\text{ }^\circ\text{C}$			0.8 1.2	V
V_{GD}	Non-Trigger Gate Voltage (1)	$V_{\text{AK}} = 12\text{ V}$, $R_L = 100$ $T_C = 125\text{ }^\circ\text{C}$	0.2			V
dv/dt	Critical Rate of Rise Off-State Voltage	$V_D = \text{Rated } V_{\text{DRM}}$, Exponential waveform, $R_{\text{GK}} = 1000$ $T_J = 125\text{ }^\circ\text{C}$	500	800		V/ μs
di/dt	Critical Rate of Rise On-State Current	$I_{\text{PK}} = 20\text{ A}$; $P_W = 10\text{ }\mu\text{s}$; $di_G/dt = 1\text{ A}/\mu\text{s}$ $I_{\text{gt}} = 20\text{ mA}$			50	A/ μs
I_{H}	Holding Current	$V_{\text{AK}} = 12\text{ V}$, Gate Open Initiating Current = 20mA $T_C = 25\text{ }^\circ\text{C}$ $T_C = -40\text{ }^\circ\text{C}$		2	5.0 10	mA
$R_{\text{th(j-c)}}$	Thermal Impedance	Junction to case			15	$^\circ\text{C}/\text{W}$
$R_{\text{th(j-a)}}$	Thermal Impedance	Junction to Ambient			125	$^\circ\text{C}/\text{W}$

Notes :

1. Pulse Width 1.0 ms , Duty cycle 1%
2. Does not include R_{GK} in measurement.

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Fig 1. Gate Characteristics

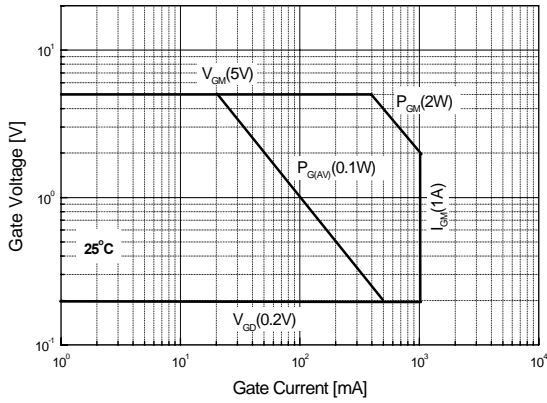


Fig 2. Maximum Case Temperature

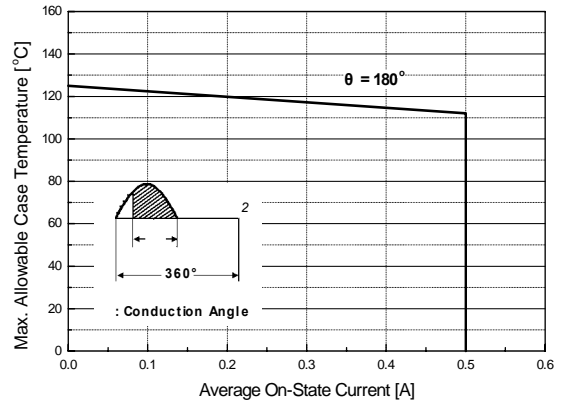


Fig 3. Typical Forward Voltage

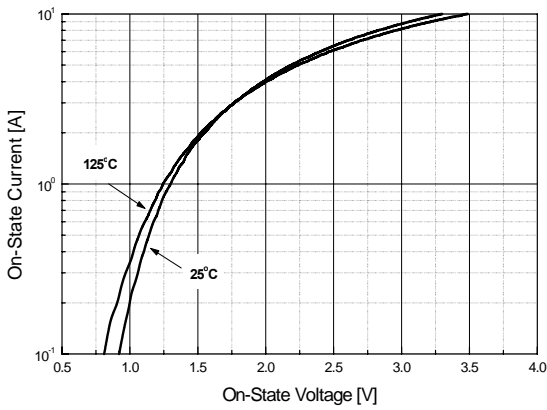


Fig 4. Thermal Response

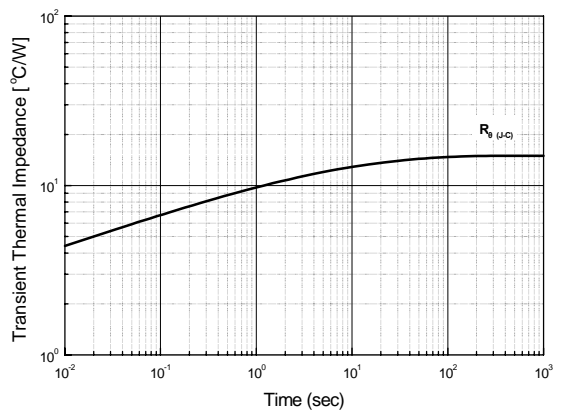


Fig 5. Typical Gate Trigger Voltage vs. Junction Temperature

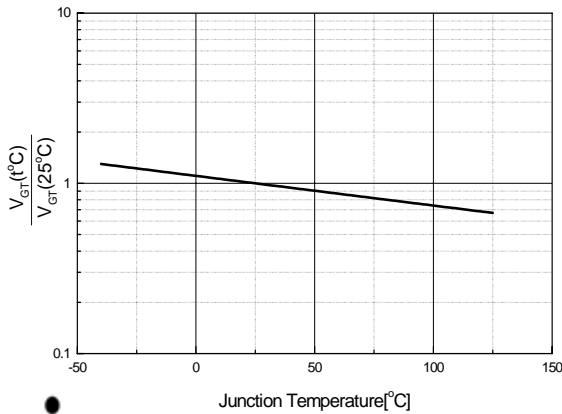
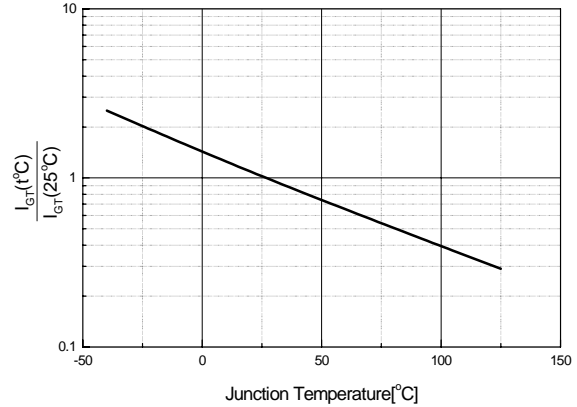


Fig 6. Typical Gate Trigger Current vs. Junction Temperature



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Fig 7. Typical Holding Current

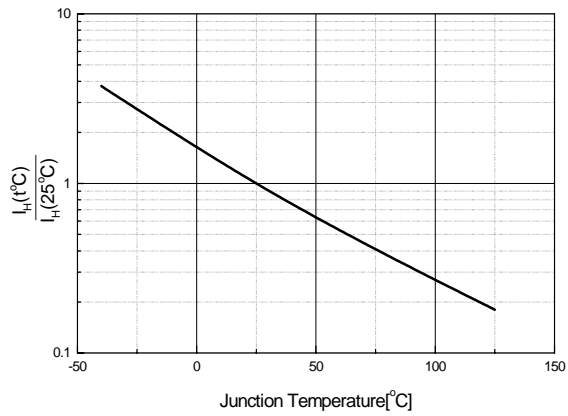
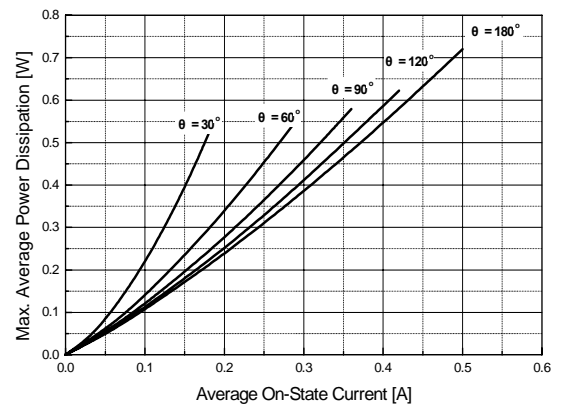


Fig 8. Power Dissipation



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SOT- 89 Package Dimension

Dim.	mm			Inch		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	1.40		1.60	0.055		0.063
B	0.36		0.56	0.014		0.022
B1	0.32		0.52	0.013		0.020
C	0.35		0.44	0.014		0.017
C1	0.35		0.44	0.014		0.017
D	4.40		4.60	0.173		0.181
D1	1.40		1.80	0.055		0.071
E	2.30		2.60	0.091		0.102
e		1.50			0.060	
e1	2.90		3.10	0.114		0.122
H	3.94		4.25	0.155		0.167
L	0.90		1.10	0.035		0.043
R		0.25			0.010	

